

# Millimeter-Wave CMOS Device Modeling and Issues

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# Outline

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- Motivation & Brief introduction of 60GHz CMOS transceiver
  - Modeling issues
    - Measurement issues
    - Substrate modeling issues
  - Layout optimization
  - Transistor characterization
  - Summary & Conclusion

# Motivation

- **60GHz CMOS transceiver for multi-Gbps wireless communication**

**IEEE 802.11ad specification**

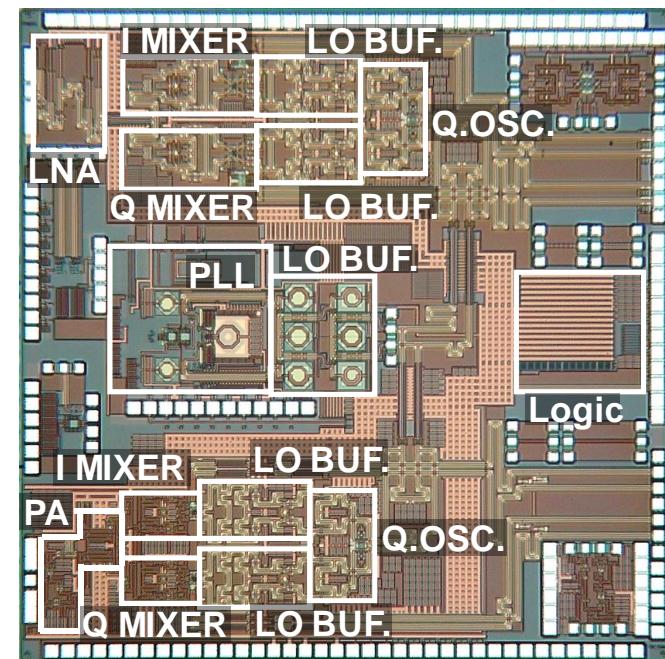
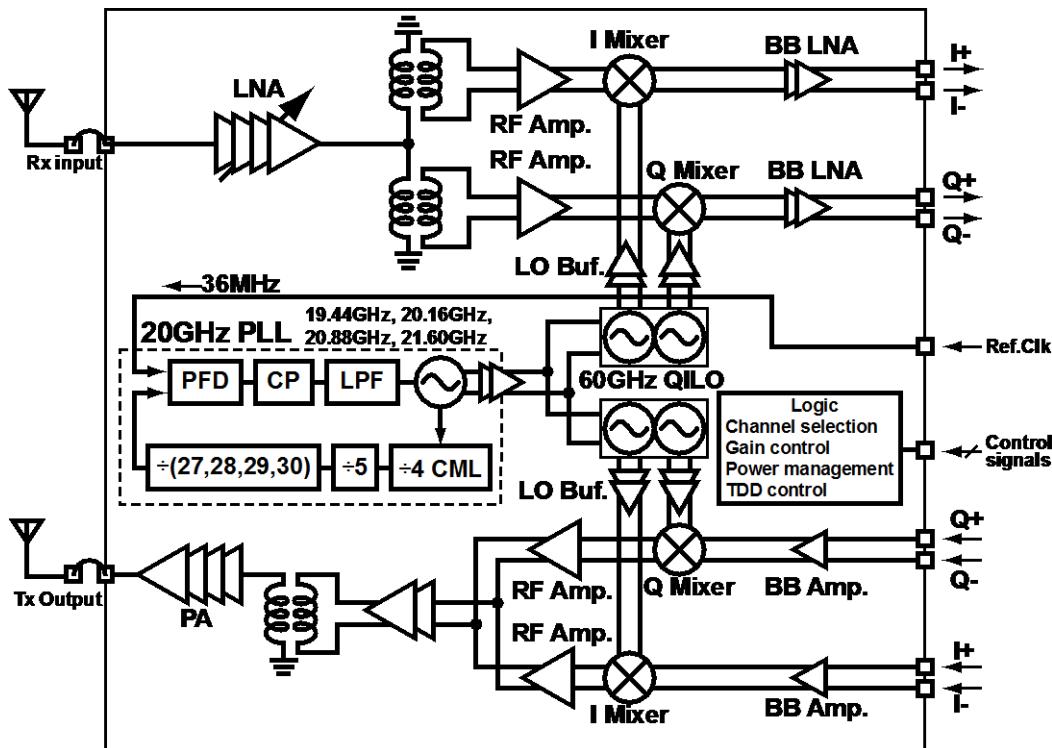
- **57.24GHz - 65.88GHz**
- **2.16GHz/ch x 4channels**



	QPSK	16QAM	64QAM
2.16GHz x1ch	3.4Gbps	6.8Gbps	10.1Gbps
2.16GHz x4ch	13.5Gbps	27.0Gbps	40.6Gbps

# 60GHz Direct-Conversion Transceiver

- 2.4GHz vs 60GHz (25x)
  - RF front-end (Tx/Rx/LO)
  - Simulation/Modeling, Gain, Noise, Pout

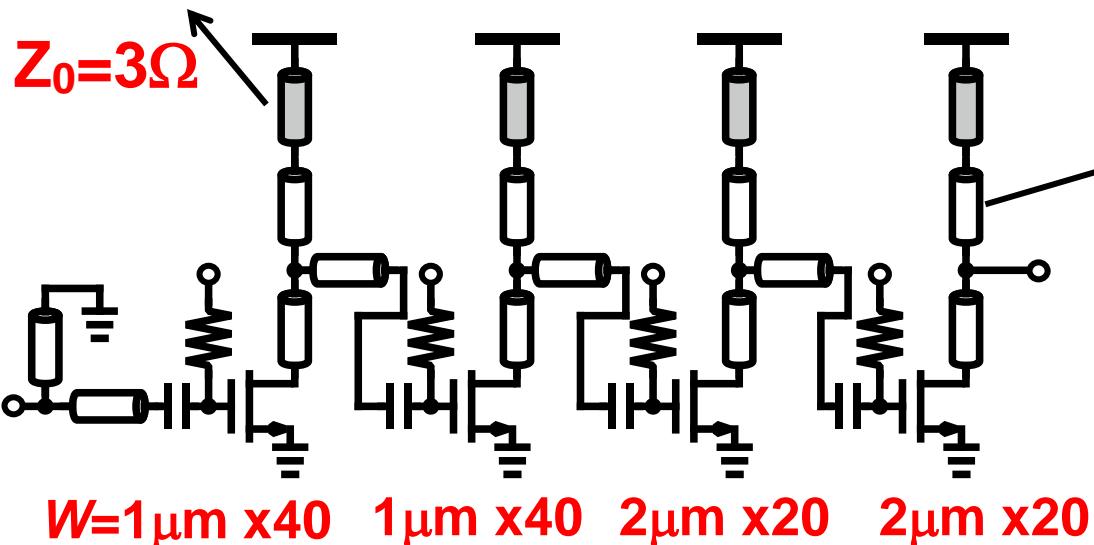


65nm CMOS, 4.2x4.2mm

# TL-Based Design

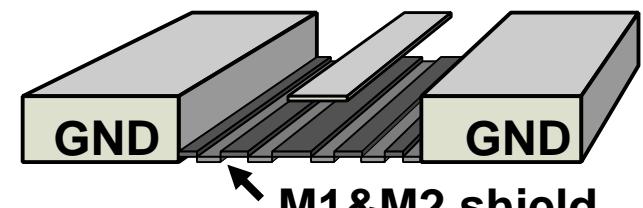
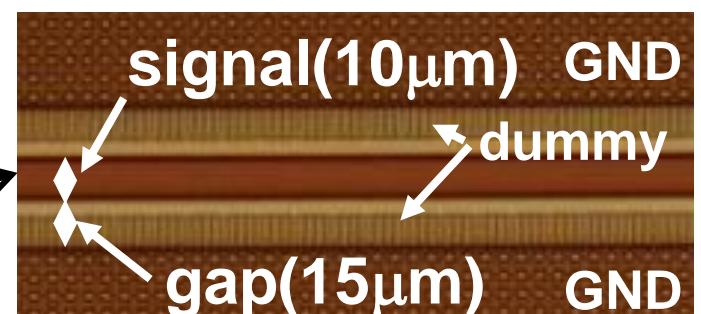
- TL-based design for simulation accuracy
- Low-loss TL & MIM TL

MIM TL for decoupling



4-stage CS-CS LNA

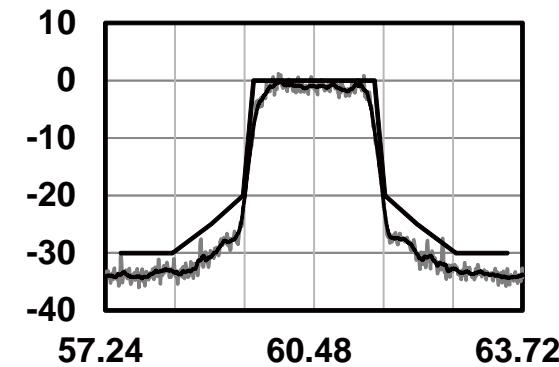
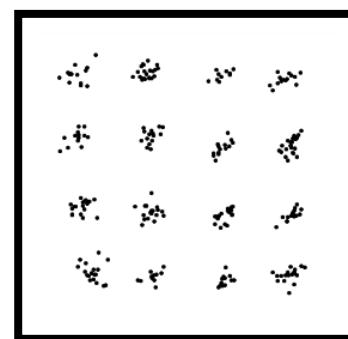
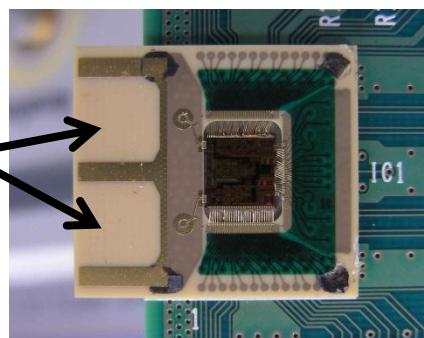
**50Ω, 0.8dB/mm**



# Performance Summary

	Arch.	Max. rate in 16QAM	Distance for BER $<10^{-3}$	$P_{DC}$ (Tx/Rx)
IMEC[3]	Direct	7Gb/s	ch.1-4 (EVM < -17dB) (w/o PLL)	176mW / 112mW
SiBeam [4]	Hetero	7Gb/s	ch.2-3 (EVM < -19dB) 50m(LOS), 16m(NLOS)	1,820mW / 1,250mW
This work	Direct	10Gb/s-	ch.1-4 (EVM < -23dB) 1.3-1.6m (QPSK) 0.3-0.5m (16QAM)	319mW / 223mW

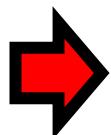
6dBi antennas



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# **Issues of mmW Tr Modeling**

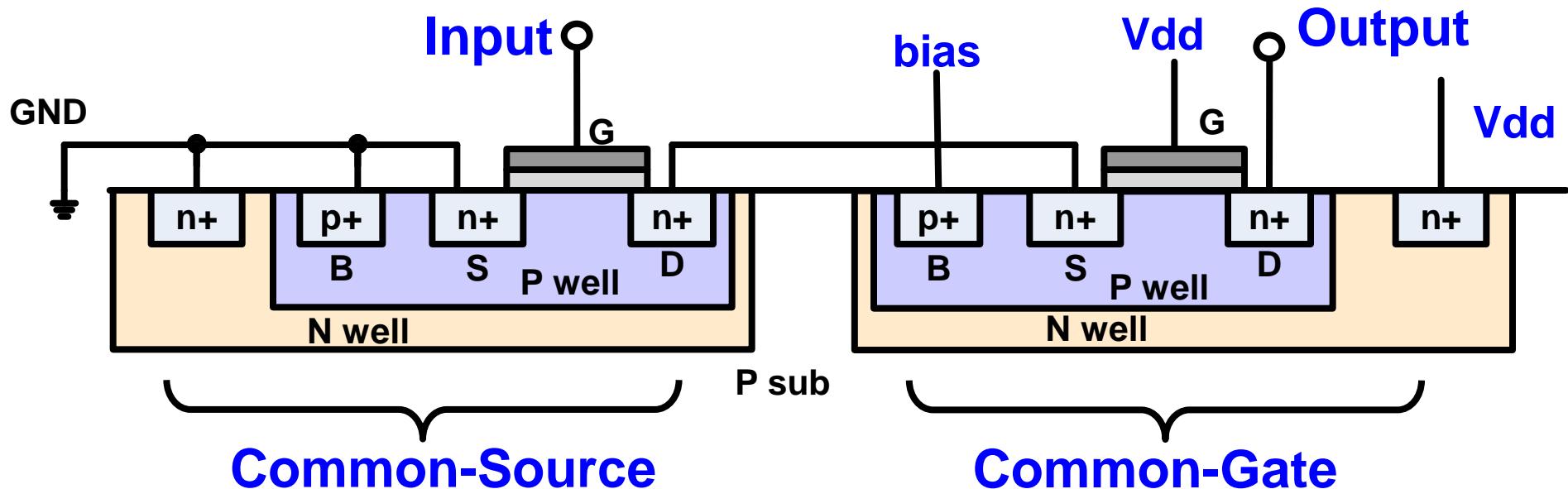
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- Bias scalability
- L & W scalability
- Linearity
  - Large-signal accuracy for RF and mmW
- Noise

**caused by**

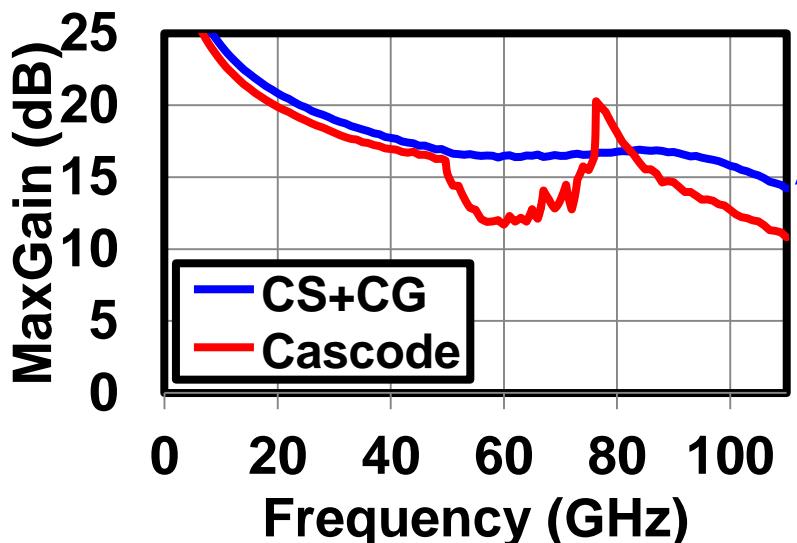
- Measurement inaccuracy
- Complex physical and electrical structure of miniaturized transistors
  - Substrate model

# Substrate Coupling



Common-Source

Common-Gate



connect S-parameters  
measured individually



completely same layout but  
different characteristics

# Substrate model issue

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- Measurement through drain, gate and source is not so reliable to build an equivalent circuit of the substrate network.
- Up to 10GHz
- CS meas. + CG meas.  $\neq$  Cascode meas.
- $L$ ,  $W_f$ -scalability,  $V_B$  dependence

# Current status & Target

	DC (< 1GHz)	RF (< 10GHz)	mmW 
Bias dep. ( $V_G$ , $V_D$ )	✓	✓	✓
Bias dep. ( $V_S$ )	✓	✓	partially
Bias dep. ( $V_B$ )	✓		
#finger scalability	✓	✓	✓
$W_f$ scalability	✓	✓	
$L$ scalability	✓		
Non-linearity (IM3)	✓	✓	partially
Large-signal	✓	partially	
Noise	✓	partially	

# Outline

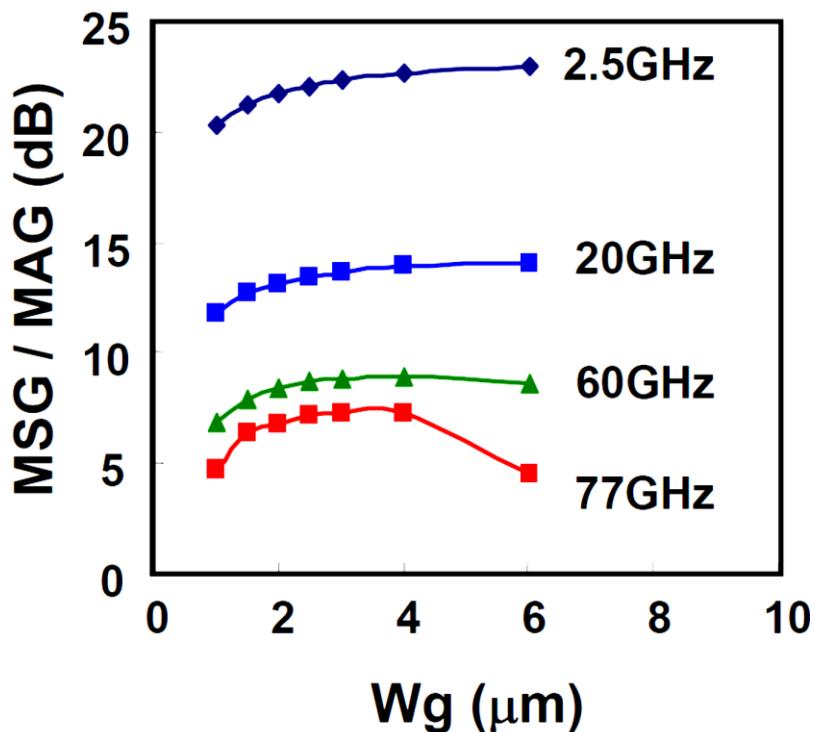
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# Finger Width Optimization

Gate-width ( $W_g$ ) dependence

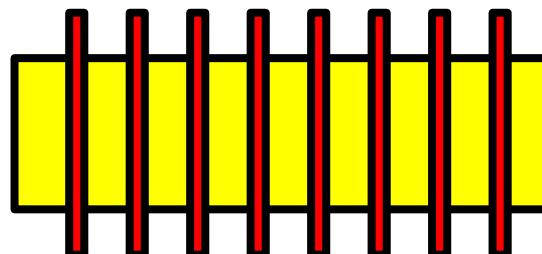
Total  $W_g$ : 80  $\mu\text{m}$



[5] T. Suzuki, ISSCC 2008

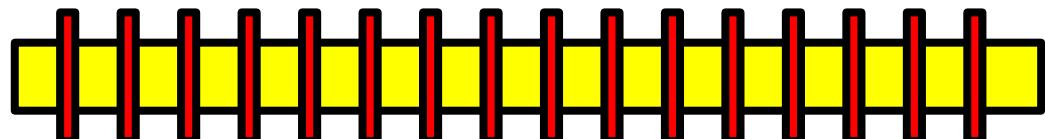
$W=2\text{um}\times 8$

- MAG peak



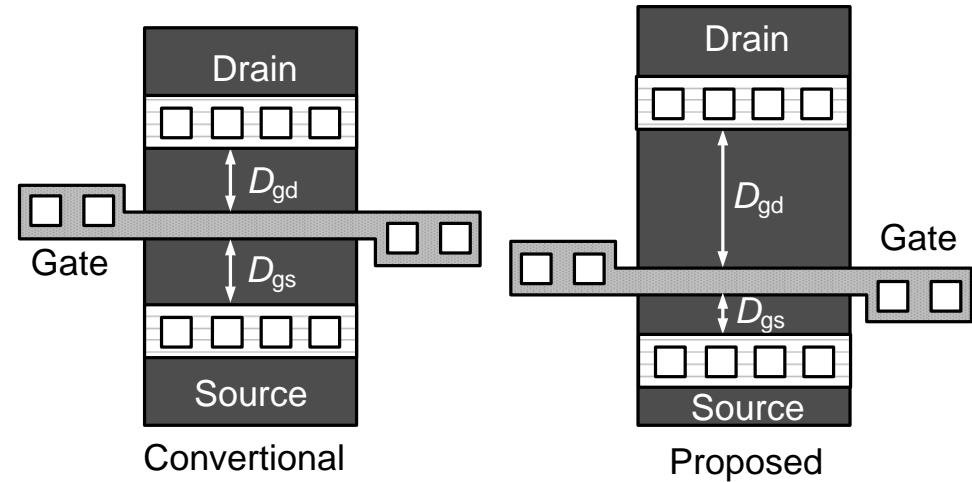
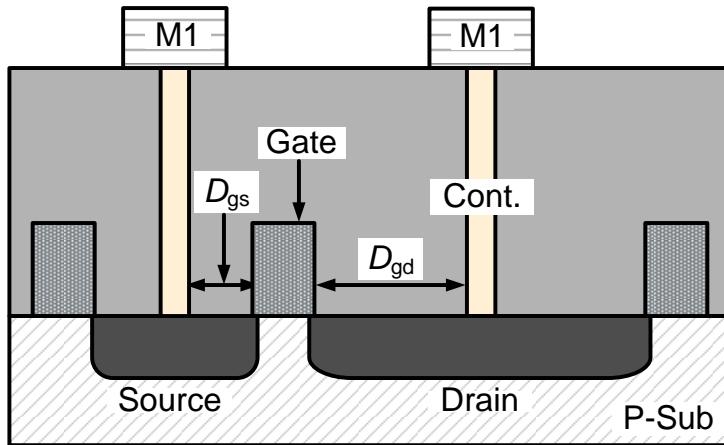
$W=1\text{um}\times 16$

- $R_g$
- Diffusion capacitance
- MAG
- NF



# Asymmetric Source/Drain Layout

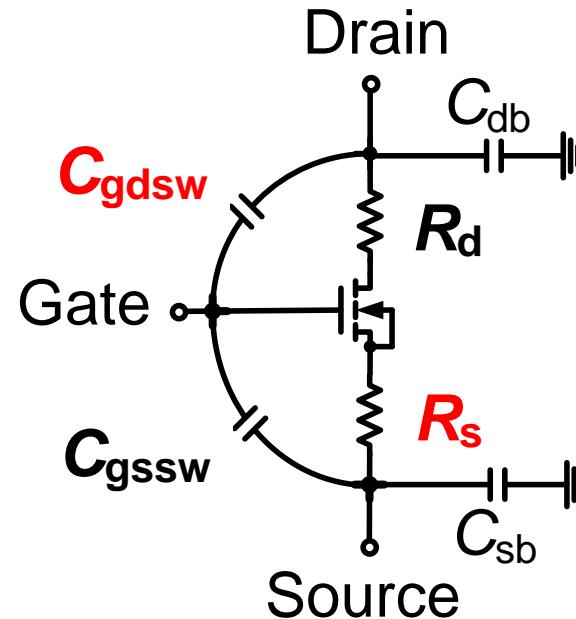
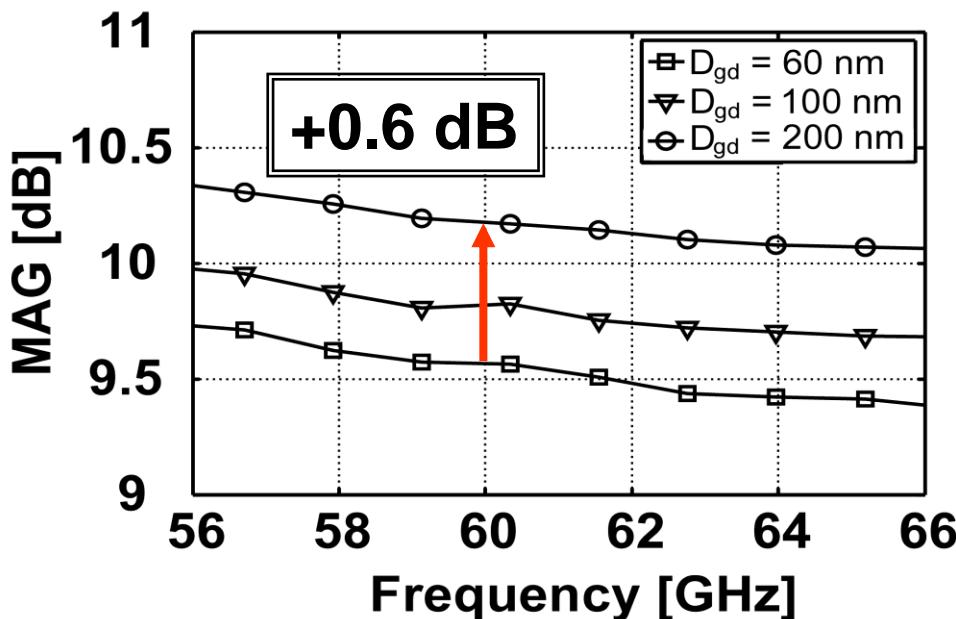
- $D_{gd}$  should be longer for smaller  $C_{gdsw}$ .
- $D_{gs}$  should be shorter for smaller  $R_s$ .



- $D_{gd}$  : Gate to drain contact distance
- $D_{gs}$  : Gate to source contact distance

# Dgd Optimization

- MAG is improved by **0.6 dB**.



- Small  $C_{gds}$  will increase  $f_{\max}$** 
  - Larger  $D_{gd}$  (e.g. 200 nm)
- Large  $R_s$  will degenerate the transistor**
  - Smallest  $D_{gs}$  (e.g. 60 nm)

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# Summary & Conclusion

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- Device models for mmW design are still not developed well as compared with lower frequency.
- $L$ ,  $W_f$ , #finger,  $V_B$ ,  $V_S$  scalability
- Noise and linearity are also headache.

# Acknowledgement

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